# Antonio R Zanatta

List of Publications by Year
in descending order

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| 132 | 2,187 | 279701 | 289141 |
|---|---|---|---|
| papers | citations | 23 h-index | 40 g-index |

| 132 | 132 | 132 | 2145 |
|---|---|---|---|
| all docs | docs citations | times ranked | citing authors |

| # | Article | IF | Citations |
|---|---|---|---|
| 1 | Gradual and selective achievement of Rutile-TiO2 by thermal annealing amorphous TixOyNz films. Journal of Non-Crystalline Solids, 2022, 579, 121375. | 1.5 | 1 |
| 2 | The optical bandgap of lithium niobate (LiNbO3) and its dependence with temperature. Results in Physics, 2022, 39, 105736. | 2.0 | 11 |
| 3 | Assessing the amount of the anatase and rutile phases of TiO2 by optical reflectance measurements. Results in Physics, 2021, 22, 103864. | 2.0 | 5 |
| 4 | Reducible oxide and allotropic transition induced by hydrogen annealing: synthesis routes of TiO2 thin films to tailor optical response. Journal of Materials Research and Technology, 2021, 12, 1623-1637. | 2.6 | 12 |
| 5 | On the relationship between the Raman scattering features and the Ti-related chemical states of TixOyNz films. Journal of Materials Research and Technology, 2021, 14, 864-870. | 2.6 | 6 |
| 6 | A sensitive temperature probe based on Er3+-doped GeOx films. Results in Physics, 2020, 16, 102871. | 2.0 | 2 |
| 7 | Role of Rare Earth Elements and Entropy on the Anatase-To-Rutile Phase Transformation of TiO<sub>2</sub> Thin Films Deposited by Ion Beam Sputtering. ACS Omega, 2020, 5, 28027-28036. | 1.6 | 12 |
| 8 | Temperature-dependent Raman scattering of the Geâ€¯+â€¯GeOx system and its potential as an optical thermometer. Results in Physics, 2020, 19, 103500. | 2.0 | 12 |
| 9 | Revisiting the optical bandgap of semiconductors and the proposal of a unified methodology to its determination. Scientific Reports, 2019, 9, 11225. | 1.6 | 215 |
| 10 | Influence of the Anatase and Rutile phases on the luminescent properties of rare-earth-doped TiO2 films. Journal of Alloys and Compounds, 2019, 780, 491-497. | 2.8 | 13 |
| 11 | Self-organized nickel nanoparticles on nanostructured silicon substrate intermediated by a titanium oxynitride (TiNxOy) interface. AIP Advances, 2018, 8, 015025. | 0.6 | 8 |
| 12 | Whitish light-emitting ZnO micro-flakes: their production and optical properties. Optical Materials Express, 2018, 8, 270. | 1.6 | 2 |
| 13 | A suitable (wide-range + linear) temperature sensor based on Tm3+ ions. Scientific Reports, 2017, 7, 14113. | 1.6 | 15 |
| 14 | A fast-reliable methodology to estimate the concentration of rutile or anatase phases of TiO2. AIP Advances, 2017, 7, . | 0.6 | 44 |
| 15 | Coexistence of Sm^3+ and Sm^2+ ions in amorphous SiO_x: origin, main light emission lines and excitation-recombination mechanisms. Optical Materials Express, 2016, 6, 2108. | 1.6 | 12 |
| 16 | An alternative experimental approach to produce rare-earth-doped SiOx films. Journal of Applied Physics, 2016, 119, . | 1.1 | 9 |
| 17 | Temperature dependence of photoluminescence from Î“â€“Î“ and Î“â€“Xminibands in lattice matched InGaAs/InP superlattices. Journal Physics D: Applied Physics, 2015, 48, 465101. | 1.3 | 2 |
| 18 | Single-Walled Carbon Nanotubes Functionalized with Carboxylic Acid for Fabricating Polymeric Composite Microstructures. Journal of Nanoscience and Nanotechnology, 2015, 15, 9797-9801. | 0.9 | 6 |

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| 19 | Photoluminescence and compositional-structural properties of ion-beam sputter deposited Er-doped TiO2â^'xNx films: Their potential as a temperature sensor. Journal of Applied Physics, 2015, 117, . | 1.1 | 16 |
| 20 | On the structural-optical properties of Al-containing amorphous Si thin films and the metal-induced crystallization phenomenon. Journal of Applied Physics, 2014, 116, 073511. | 1.1 | 7 |
| 21 | Influence of Ni concentration on the crystallization of amorphous Si films and on the development of different Ni-silicide phases. Journal of Applied Physics, 2014, 116, 123508. | 1.1 | 3 |
| 22 | Concentration quenching of the green photoluminescence from terbium ions embedded in AlN and SiC matrices. Journal of Luminescence, 2013, 137, 73-76. | 1.5 | 16 |
| 23 | Concentration quenching and thermal activation of the luminescence from terbiumâ€doped a â€SiC:H and c â€AlN thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2013, 10, 68-71. | 0.8 | 8 |
| 24 | The Thermo Optic Coefficient of Amorphous SiN Films in the Near-Infrared and Visible Regions and Its Experimental Determination. Applied Physics Express, 2013, 6, 042402. | 1.1 | 18 |
| 25 | Efficient 1535 nm light emission from an all-Si-based optical micro-cavity containing Er^3+ and Yb^3+ ions. Optics Express, 2013, 21, 28394. | 1.7 | 3 |
| 26 | A simple-versatile approach to achieve all-Si-based optical micro-cavities. Journal of Applied Physics, 2013, 113, . | 1.1 | 4 |
| 27 | RAMAN SPECTROSCOPY OF TEMPERATURE INDUCED EFFECTS IN FOUR CARBON ALLOTROPES. Modern Physics Letters B, 2013, 27, 1350203. | 1.0 | 2 |
| 28 | Quantum-plasmonic interaction: emission enhancement of Er3+- Tm3+co-doped tellurite glass via tuning nanobowtie. , 2013, , . | | 3 |
| 29 | Visible light emission and energy transfer processes in Sm-doped nitride films. Journal of Applied Physics, 2012, 111, . | 1.1 | 8 |
| 30 | Enhancement of optical absorption by modulation of the oxygen flow of TiO2 films deposited by reactive sputtering. Journal of Applied Physics, 2012, 111, . | 1.1 | 28 |
| 31 | Surface plasmon propagation in novel multilayered metallic thin films. , 2012, , . | | 2 |
| 32 | Integrated hybrid plasmonic cavity with in-plane photon-plasmon coupling for luminescence enhancement. , 2012, , . | | 0 |
| 33 | Luminescence enhancement of Er3+ions from electric multipole nanostructure arrays. , 2012, , . | | 4 |
| 34 | Focusing surface plasmons on Er3+ ions through gold planar plasmonic lenses. Applied Physics A: Materials Science and Processing, 2012, 109, 1037-1041. | 1.1 | 11 |
| 35 | Tailored SERS substrates obtained with cathodic arc plasma ion implantation of gold nanoparticles into a polymer matrix. Physical Chemistry Chemical Physics, 2012, 14, 2050. | 1.3 | 21 |
| 36 | Exponential depletion of neutral dangling bonds density (D0) by rare-earth doping in amorphous Si films. Physica B: Condensed Matter, 2012, 407, 3222-3224. | 1.3 | 1 |

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| 37 | Integrated plasmonic MoirÃ© cavity in photonic crystal cavity for luminescence enhancement. , 2012, , . | | 1 |
| 38 | Focusing surface plasmons on Er3+ions with convex/concave plasmonic lenses. , 2012, , . | | 4 |
| 39 | Effect of O2+, H2++â€‰O2+, and N2++â€‰O2+ ion-beam irradiation on the field emission properties of carbon nanotubes. Journal of Applied Physics, 2011, 109, 114317. | 1.1 | 6 |
| 40 | Influence of film thickness on the optical transmission through subwavelength single slits in metallic thin films. Applied Optics, 2011, 50, G11. | 2.1 | 18 |
| 41 | Development of the MnSi1.7 phase in Mn-containing Si films. Materials Chemistry and Physics, 2011, 129, 148-153. | 2.0 | 12 |
| 42 | Structuralâ€“electronic aspects related to the near-infrared light emission of Fe-doped silicon films. Solid State Communications, 2011, 151, 587-590. | 0.9 | 0 |
| 43 | Raman spectroscopy analysis of structural photoinduced changes in GeS2+Ga2O3 thin films. Current Applied Physics, 2010, 10, 1411-1415. | 1.1 | 5 |
| 44 | Effect of Mn concentration and atomic structure on the magnetic properties of Ge thin films. Journal of Applied Physics, 2010, 108, 113922. | 1.1 | 7 |
| 45 | Influence of chromium concentration on the opticalâ€“electronic properties of ruby microstructures. Journal Physics D: Applied Physics, 2010, 43, 015302. | 1.3 | 7 |
| 46 | Structural, optical and morphological characterization of amorphous Ge<sub>100â^'x</sub>Mn<sub>x</sub>films deposited by sputtering. Journal Physics D: Applied Physics, 2009, 42, 035005. | 1.3 | 10 |
| 47 | Evidence of magnetic vortices formation in Mn-based sub-micrometre structures embedded in Siâ€“Mn films. Journal Physics D: Applied Physics, 2009, 42, 132002. | 1.3 | 6 |
| 48 | Effect of thermal annealing treatments on the optical properties of rare-earth-doped AlN films. Journal Physics D: Applied Physics, 2009, 42, 025109. | 1.3 | 27 |
| 49 | Electrophoretic deposition of Ba0.77Ca0.23TiO3 nanopowders. Journal of Materials Processing Technology, 2008, 203, 526-531. | 3.1 | 8 |
| 50 | Resonant excitation of Mn local vibrational modes in the higher order Raman spectra of nanocrystalline Ga1â^'xMnxN films. Journal of Physics Condensed Matter, 2008, 20, 252201. | 0.7 | 5 |
| 51 | Influence of film thickness on the crystallization of Ni-doped amorphous silicon samples. Journal of Applied Physics, 2008, 104, . | 1.1 | 8 |
| 52 | Aluminium-induced nanocrystalline Ge formation at low temperatures. Journal of Physics Condensed Matter, 2007, 19, 076206. | 0.7 | 12 |
| 53 | Redâ€“greenâ€“blue light emission and energy transfer processes in amorphous SiN films doped with Sm and Tb. Journal of Physics Condensed Matter, 2007, 19, 436230. | 0.7 | 7 |
| 54 | Crystallization, stress, and stress-relieve due to nickel in amorphous silicon thin films. Journal of Applied Physics, 2007, 102, . | 1.1 | 11 |

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| 55 | Amorphous BeN as a new solid host for rare-earth-related luminescent materials. Physica Status Solidi - Rapid Research Letters, 2007, 1, 153-155. | 1.2 | 4 |
| 56 | Thermally synthesized ruby microstructures and luminescence centers. Journal of Applied Physics, 2006, 100, 113112. | 1.1 | 5 |
| 57 | Spectroscopic investigation of Nd-doped amorphous SiN films. Journal of Non-Crystalline Solids, 2006, 352, 1286-1289. | 1.5 | 0 |
| 58 | Metal-induced nanocrystalline structures in Ni-containing amorphous silicon thin films. Journal of Applied Physics, 2006, 100, 094311. | 1.1 | 26 |
| 59 | Thermal activation, cathodo- and photoluminescence measurements of rare earth doped (Tm,Tb,Dy,Eu,Sm,Yb) amorphous/nanocrystalline AlN thin films prepared by reactive rf-sputtering. Optical Materials, 2006, 28, 790-793. | 1.7 | 48 |
| 60 | Crystallization, texture and second-harmonic generation in TiO2â€“BaOâ€“B2O3 glasses. Optical Materials, 2006, 28, 935-943. | 1.7 | 20 |
| 61 | Optical properties of Er and Er+Yb doped hydrogenated amorphous silicon films. Journal of Physics Condensed Matter, 2006, 18, 7709-7716. | 0.7 | 5 |
| 62 | Effect of the initial structure of silicon surface on the generation of multiple structural phases by cyclic microindentation. Applied Physics Letters, 2006, 89, 031917. | 1.5 | 16 |
| 63 | Annealing effects on crystallized Al-doped a-Ge:H thin films. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 3750-3753. | 0.8 | 0 |
| 64 | Annealing crystallization of a-Ge/Al/Si and a-Ge/Si thin films. Physica Status Solidi (B): Basic Research, 2005, 242, 1906-1909. | 0.7 | 1 |
| 65 | Low-temperature Al-induced crystallization of amorphous Ge. Journal of Applied Physics, 2005, 97, 094914. | 1.1 | 45 |
| 66 | Optoelectronic and structural characteristics of Er-doped amorphous AlN films. Journal of Applied Physics, 2005, 98, 093514. | 1.1 | 19 |
| 67 | Formation of silicon nanocrystals in SiO[sub 2] by oxireduction reaction induced by impurity implantation and annealing. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2004, 22, 1669. | 1.6 | 4 |
| 68 | Spectroscopic study of Nd-doped amorphous SiN films. Journal of Applied Physics, 2004, 96, 1068-1073. | 1.1 | 16 |
| 69 | Synthesis and Characterization of the Â-BaB2O4Phase Obtained by the Polymeric Precursor Method. Journal of Sol-Gel Science and Technology, 2004, 29, 89-96. | 1.1 | 17 |
| 70 | Î²-BaB2O4 nanometric powder obtained from the ternary BaOâ€“B2O3â€“TiO2 system using the polymeric precursor method. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 107, 33-38. | 1.7 | 12 |
| 71 | Synthesis and characterization of beta barium borate thin films obtained from the BaOâ€“B2O3â€“TiO2 ternary system. Thin Solid Films, 2004, 457, 246-252. | 0.8 | 7 |
| 72 | Laser-induced generation of micrometer-sized luminescent patterns on rare-earth-doped amorphous films. Journal of Applied Physics, 2004, 96, 5977-5981. | 1.1 | 17 |

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| 73 | Comprehensive spectroscopic study of nitrogenated carbon nanotubes. Physical Review B, 2004, 69, . | 1.1 | 65 |
| 74 | Photoluminescence of a-GeN alloys doped with different rare-earth ions. Journal of Non-Crystalline Solids, 2004, 338-340, 469-472. | 1.5 | 5 |
| 75 | Photon and electron excitation of rare-earth-doped amorphous SiN films. Journal of Non-Crystalline Solids, 2004, 338-340, 473-476. | 1.5 | 10 |
| 76 | Amorphous hydrogenated carbon films deposited by PECVD: influence of the substrate temperature on film growth and microstructure. Journal of Non-Crystalline Solids, 2004, 338-340, 503-508. | 1.5 | 14 |
| 77 | Thermal lens and non-linear optical absorption study of a-SiH films. Journal of Non-Crystalline Solids, 2004, 348, 230-234. | 1.5 | 5 |
| 78 | Neutral dangling bond depletion in amorphous SiN films induced by magnetic rare-earth elements. Solid State Communications, 2003, 128, 47-50. | 0.9 | 1 |
| 79 | Unusual Interactions Binding Iron Tetrasulfonated Phthalocyanine and Poly(allylamine) Tj ETQq1 1 0.784314 rgBT /Overlock 10 Tf 50 | 1.2 | 100 |
| 80 | X-ray photoelectron spectroscopic study of rare-earth-doped amorphous siliconâ€“nitrogen films. Journal of Applied Physics, 2003, 93, 1948-1953. | 1.1 | 9 |
| 81 | Photoluminescence quenching in Er-doped compounds. Applied Physics Letters, 2003, 82, 1395-1397. | 1.5 | 50 |
| 82 | Magnetic properties of amorphous Si films doped with rare-earth elements. Physical Review B, 2003, 68, . | 1.1 | 8 |
| 83 | Synthesis and spectroscopic investigation of ruby microstructures. Applied Physics Letters, 2003, 83, 2336-2338. | 1.5 | 4 |
| 84 | Laser Interference Structuring of a-GeN for the Production of Optical Diffraction Gratings. Materials Research Society Symposia Proceedings, 2003, 762, 1741. | 0.1 | 0 |
| 85 | Laser interference structuring of a-Ge films on GaAs. Journal of Applied Physics, 2002, 91, 2916-2920. | 1.1 | 4 |
| 86 | Optical diffraction gratings produced by laser interference structuring of amorphous germaniumâ€“nitrogen alloys. Applied Physics Letters, 2002, 81, 2731-2733. | 1.5 | 5 |
| 87 | Structural properties of aluminumâ€“nitrogen films prepared at low temperature. Applied Physics Letters, 2002, 81, 1005-1007. | 1.5 | 24 |
| 88 | Comment on â€œIon-assisted pulsed laser deposition of aluminum nitride thin filmsâ€•[J. Appl. Phys.87, 1540 (2000)]. Journal of Applied Physics, 2002, 92, 6349-6350. | 1.1 | 1 |
| 89 | Pulsed laser crystallization and structuring of a-Ge on GaAs. Journal of Non-Crystalline Solids, 2002, 299-302, 137-142. | 1.5 | 2 |
| 90 | Microscopic mechanisms behind the Al-induced crystallization of a-Ge:H films. Journal of Non-Crystalline Solids, 2002, 299-302, 143-147. | 1.5 | 8 |

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| 91 | X-ray photoelectron spectroscopy of amorphous AlN alloys prepared by reactive rf sputtering. Journal of Non-Crystalline Solids, 2002, 299-302, 323-327. | 1.5 | 4 |
| 92 | Red and Green Light Emission From Samarium-Doped Amorphous Aluminum Nitride Films. Advanced Materials, 2002, 14, 1154. | 11.1 | 15 |
| 93 | Plasma deposition of amorphous carbon films from CH4 atmospheres highly diluted in Ar. Thin Solid Films, 2002, 419, 46-53. | 0.8 | 24 |
| 94 | Magnetic properties of gadolinium-doped amorphous silicon films. Brazilian Journal of Physics, 2002, 32, 409-411. | 0.7 | 4 |
| 95 | Structural properties of hydrogenated carbon-nitride films produced by ion-beam-assisted evaporation of the molecular precursor C4N6H4. Journal of Applied Physics, 2001, 89, 7852-7859. | 1.1 | 2 |
| 96 | Visible luminescence from a-SiN films doped with Er and Sm. Applied Physics Letters, 2001, 79, 488-490. | 1.5 | 33 |
| 97 | Epitaxial pulsed laser crystallization of amorphous germanium on GaAs. Journal of Applied Physics, 2001, 90, 2575-2581. | 1.1 | 9 |
| 98 | Aluminum-induced crystallization of hydrogenated amorphous germanium thin films. Applied Physics Letters, 2001, 79, 3233-3235. | 1.5 | 39 |
| 99 | Optoelectronic and structural properties of Er-doped sputter-deposited galliumâ€“arsenicâ€“nitrogen films. Journal of Applied Physics, 2001, 90, 2321-2328. | 1.1 | 3 |
| 100 | Effects of SiH[sub 2]Cl[sub 2] on the Deposition and Properties of Amorphous and Microcrystalline Silicon Fabricated from Very High Frequency Glow Discharges. Journal of the Electrochemical Society, 2000, 147, 1829. | 1.3 | 6 |
| 101 | Optical study of thermally annealed Er-doped hydrogenatedaâˆ’Sifilms. Physical Review B, 2000, 62, 2016-2020. | 1.1 | 16 |
| 102 | Infrared photoluminescence from Er-doped a-GaAsN alloys. Journal of Non-Crystalline Solids, 2000, 266-269, 854-858. | 1.5 | 1 |
| 103 | Microcrystalline silicon with high electron field-effect mobility deposited at 230Â°C. Journal of Non-Crystalline Solids, 2000, 266-269, 1260-1264. | 1.5 | 31 |
| 104 | Photoelectron spectroscopic study of amorphous GaAsN films. Applied Physics Letters, 2000, 76, 2211-2213. | 1.5 | 10 |
| 105 | Visible photoluminescence fromEr3+ions inaâˆ’SiNalloys. Physical Review B, 1999, 59, 10091-10098. | 1.1 | 20 |
| 106 | 1540 nm light emission from Er-doped amorphous GaAsN films. Applied Physics Letters, 1999, 75, 3279-3281. | 1.5 | 13 |
| 107 | Optical and structural properties of laser annealed Er-doped amorphous silicon thin films. Journal of Applied Physics, 1999, 86, 701-703. | 1.1 | 15 |
| 108 | Optical excitation of Er3+ ions in a-SiN alloys. Journal of Applied Physics, 1999, 86, 338-341. | 1.1 | 13 |

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| 109 | 1.54 Î¼m photoluminescence of Er-containing N-doped a-Si:H. Journal of Non-Crystalline Solids, 1998, 227-230, 389-393. | 1.5 | 3 |
| 110 | Erbium luminescence in a-Si:H. Journal of Non-Crystalline Solids, 1998, 227-230, 399-402. | 1.5 | 7 |
| 111 | Green photoluminescence from Er-containing amorphous SiN thin films. Applied Physics Letters, 1998, 72, 3127-3129. | 1.5 | 70 |
| 112 | Optical spectroscopy of Er3+ and Yb3+ co-doped fluoroindate glasses. Journal of Applied Physics, 1998, 83, 2256-2260. | 1.1 | 49 |
| 113 | Nitrogen in germanium. Journal of Applied Physics, 1998, 84, 1-30. | 1.1 | 102 |
| 114 | Exponential absorption edge and disorder in Column IV amorphous semiconductors. Journal of Applied Physics, 1998, 84, 5184-5190. | 1.1 | 31 |
| 115 | Infrared spectroscopy of Er-containing amorphous silicon thin films. Applied Physics Letters, 1997, 71, 3679-3681. | 1.5 | 16 |
| 116 | Erbium luminescence from hydrogenated amorphous silicon-erbium prepared by cosputtering. Applied Physics Letters, 1997, 70, 511-513. | 1.5 | 59 |
| 117 | Electronic structure of amorphous germanium-nitrogen alloys: a UV photoelectron spectroscopy study. Journal of Non-Crystalline Solids, 1996, 198-200, 136-139. | 1.5 | 2 |
| 118 | Absorption edge, band tails, and disorder of amorphous semiconductors. Physical Review B, 1996, 53, 3833-3836. | 1.1 | 156 |
| 119 | XPS study of non-stoichiometric amorphous GeN alloys (a-GeNx, 0â‰xâ‰0.3). AIP Conference Proceedings, 1996, , . | 0.3 | 3 |
| 120 | Valence band structure of amorphous germanium-nitrogen alloys. AIP Conference Proceedings, 1996, , . | 0.3 | 2 |
| 121 | Bond distribution and structure of amorphous germaniumâ€nitrogen alloys. Physica Status Solidi (B): Basic Research, 1996, 193, 399-410. | 0.7 | 6 |
| 122 | Study of structural changes in amorphous germaniumâ€“nitrogen alloys by optical techniques. Journal of Applied Physics, 1996, 79, 433-438. | 1.1 | 10 |
| 123 | The Perspectives of Hydrogenated Amorphous Germanium as an Electronic Material. Physica Status Solidi (B): Basic Research, 1995, 192, 241-251. | 0.7 | 5 |
| 124 | Local electronegativity and chemical shift in Si and Ge based molecules and alloys. Solid State Communications, 1995, 95, 207-210. | 0.9 | 12 |
| 125 | Study of amorphous germaniumâ€nitrogen alloys through xâ€ray photoelectron and Auger electron spectroscopies. Applied Physics Letters, 1995, 66, 1258-1260. | 1.5 | 10 |
| 126 | Photoelectron spectroscopy of shallow core levels using He II(40.8 eV) excitation. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1995, 13, 2278-2280. | 0.9 | 2 |

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| 127 | Photoconductivity of intrinsic and nitrogenâ€doped hydrogenated amorphous germanium thin films. Journal of Applied Physics, 1994, 75, 4662-4667. | 1.1 | 12 |
| 128 | Infrared absorption and composition of amorphous germanium-nitrogen alloys. Journal of Physics Condensed Matter, 1993, 5, A313-A314. | 0.7 | 1 |
| 129 | On the doping efficiency of nitrogen in hydrogenated amorphous germanium. Applied Physics Letters, 1993, 62, 58-60. | 1.5 | 19 |
| 130 | Nitrogen in the amorphous-germanium network: From high dilution to the alloy phase. Physical Review B, 1993, 48, 4560-4570. | 1.1 | 34 |
| 131 | Transport properties of nitrogen-doped hydrogenated amorphous germanium films. Physical Review B, 1992, 46, 2119-2125. | 1.1 | 30 |
| 132 | Extended x-ray-absorption fine-structure investigation of short-range order ina-Ge1â^'xSnxalloys. Physical Review B, 1992, 46, 6718-6723. | 1.1 | 15 |